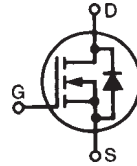


TrenchT2™ Power MOSFET

IXTA220N04T2 IXTP220N04T2

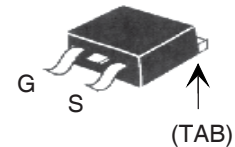
$V_{DSS} = 40V$
 $I_{D25} = 220A$
 $R_{DS(on)} \leq 3.5m\Omega$

N-Channel Enhancement Mode
Avalanche Rated

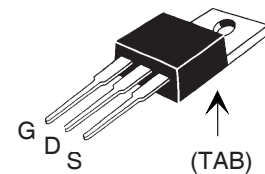


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 40 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 40 | V |
| V_{GSM} | Transient | ± 20 | V |
| I_{D25} | $T_C = 25^\circ C$ | 220 | A |
| I_{LRMS} | Lead Current Limit, RMS | 75 | A |
| I_{DM} | $T_C = 25^\circ C$, pulse width limited by T_{JM} | 660 | A |
| I_{AR} | $T_C = 25^\circ C$ | 110 | A |
| E_{AS} | $T_C = 25^\circ C$ | 600 | mJ |
| P_D | $T_C = 25^\circ C$ | 360 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | 1.6mm (0.062in.) from case for 10s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic body for 10 seconds | 260 | $^\circ C$ |
| M_d | Mounting torque (TO-220) | 1.13/10 | Nm/lb.in. |
| Weight | TO-263 | 2.5 | g |
| | TO-220 | 3.0 | g |

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- 175 $^\circ C$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-mode power supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

| Symbol | Test Conditions ($T_J = 25^\circ C$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 40 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.0 | | V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 5 μA |
| | $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 50 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2 | 2.8 | 3.5 | $m\Omega$ |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1 | 40 | 66 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 6820 | pF |
| C_{oss} | | | 1185 | pF |
| C_{rss} | | | 250 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External) | | 15 | ns |
| t_r | | | 21 | ns |
| $t_{d(off)}$ | | | 31 | ns |
| t_f | | | 21 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 112 | nC |
| Q_{gs} | | | 33 | nC |
| Q_{gd} | | | 30 | nC |
| R_{thJC} | | | 0.42 | $^\circ\text{C/W}$ |
| R_{thCH} | TO-220 | 0.50 | | $^\circ\text{C/W}$ |

Source-Drain Diode

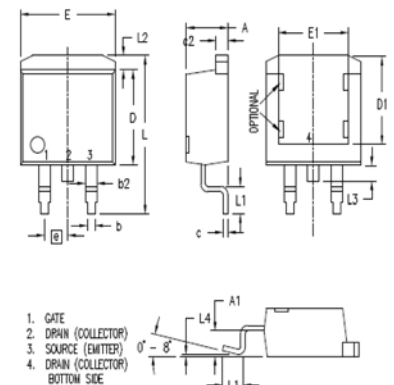
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 220 A |
| I_{SM} | Repetitive, Pulse width limited by T_{JM} | | | 660 A |
| V_{SD} | $I_F = 50\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.0 V |
| t_{rr} | $I_F = 110\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 20\text{V}$ | | 45 | ns |
| I_{RM} | | | 1.4 | A |
| Q_{RM} | | | 32 | nC |

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

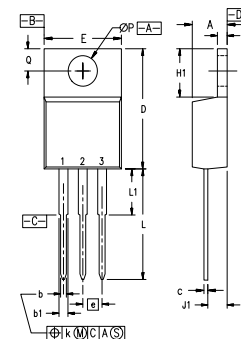
TO-263 (IXTA) Outline



- GATE (COLLECTOR)
- DRAIN (COLLECTOR)
- SOURCE (EMITTER)
- DRAIN (COLLECTOR) BOTTOM SIDE

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .160 | .190 | 4.06 | 4.83 |
| A1 | .080 | .110 | 2.03 | 2.79 |
| b | .020 | .039 | 0.51 | 0.99 |
| b2 | .045 | .055 | 1.14 | 1.40 |
| c | .016 | .029 | 0.40 | 0.74 |
| c2 | .045 | .055 | 1.14 | 1.40 |
| D | .340 | .380 | 8.64 | 9.65 |
| D1 | .315 | .350 | 8.00 | 8.89 |
| E | .380 | .410 | 9.65 | 10.41 |
| E1 | .245 | .320 | 6.22 | 8.13 |
| e | .100 BSC | | 2.54 BSC | |
| L | .575 | .625 | 14.61 | 15.88 |
| L1 | .090 | .110 | 2.29 | 2.79 |
| L2 | .040 | .055 | 1.02 | 1.40 |
| L3 | .050 | .070 | 1.27 | 1.78 |
| L4 | 0 | .005 | 0 | 0.13 |

TO-220 (IXTP) Outline



- Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .190 | 4.32 | 4.83 |
| b | .025 | .040 | 0.64 | 1.02 |
| b1 | .045 | .065 | 1.15 | 1.65 |
| c | .014 | .022 | 0.35 | 0.56 |
| D | .580 | .630 | 14.73 | 16.00 |
| E | .390 | .420 | 9.91 | 10.66 |
| e | .100 BSC | | 2.54 BSC | |
| F | .045 | .055 | 1.14 | 1.40 |
| H1 | .230 | .270 | 5.85 | 6.85 |
| J1 | .090 | .110 | 2.29 | 2.79 |
| k | 0 | .015 | 0 | 0.38 |
| L | .500 | .550 | 12.70 | 13.97 |
| L1 | .110 | .230 | 2.79 | 5.84 |
| ØP | .139 | .161 | 3.53 | 4.08 |
| Q | .100 | .125 | 2.54 | 3.18 |

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

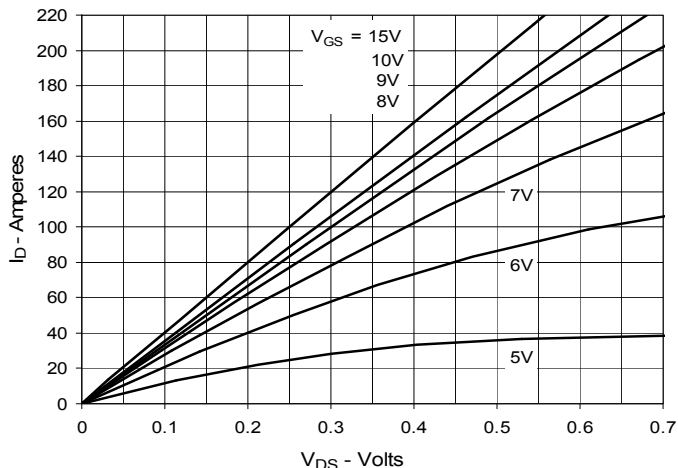


Fig. 2. Extended Output Characteristics @ 25°C

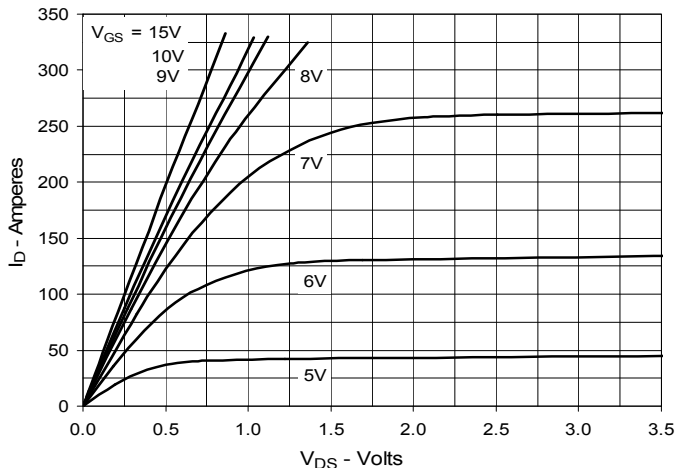


Fig. 3. Output Characteristics @ 150°C

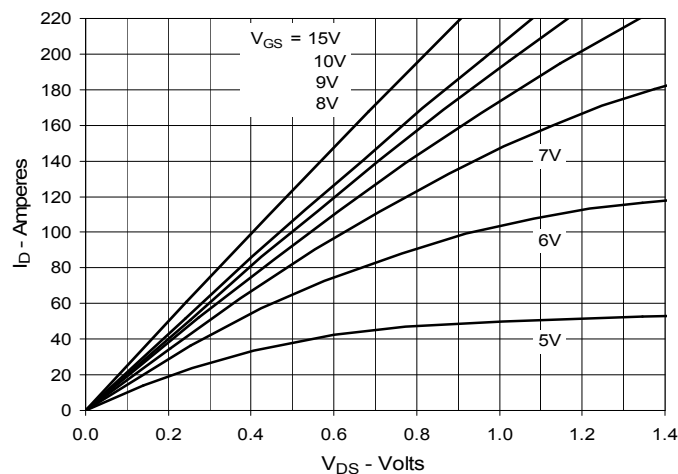


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Junction Temperature

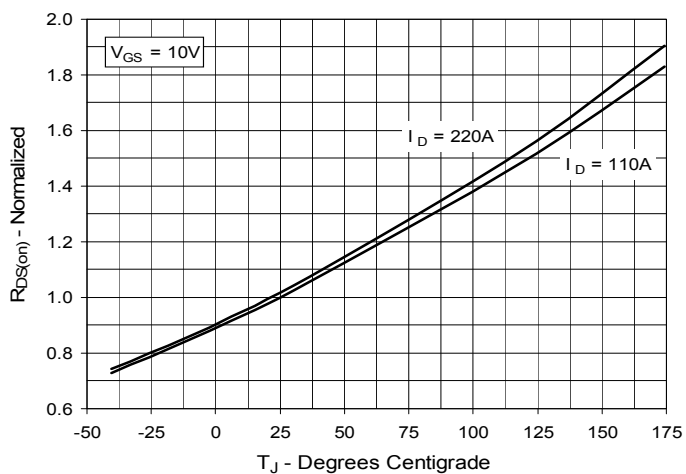


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Drain Current

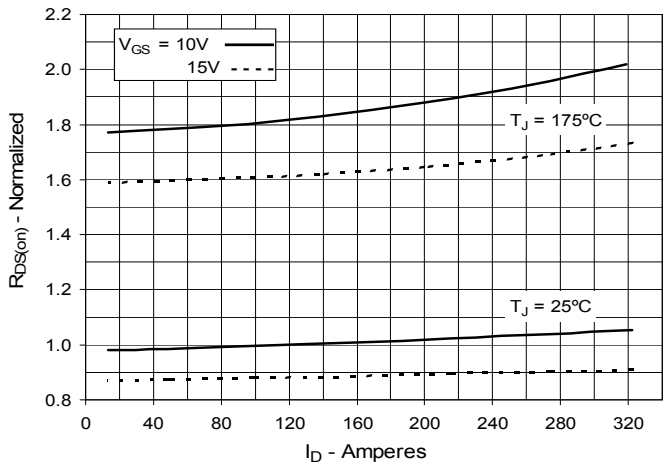


Fig. 6. Drain Current vs. Case Temperature

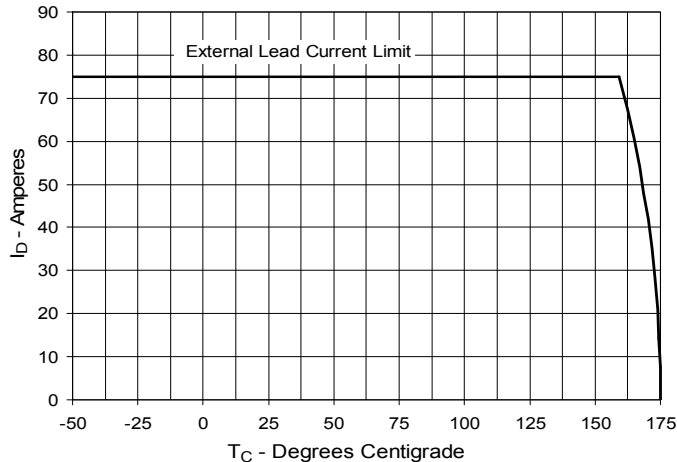


Fig. 7. Input Admittance

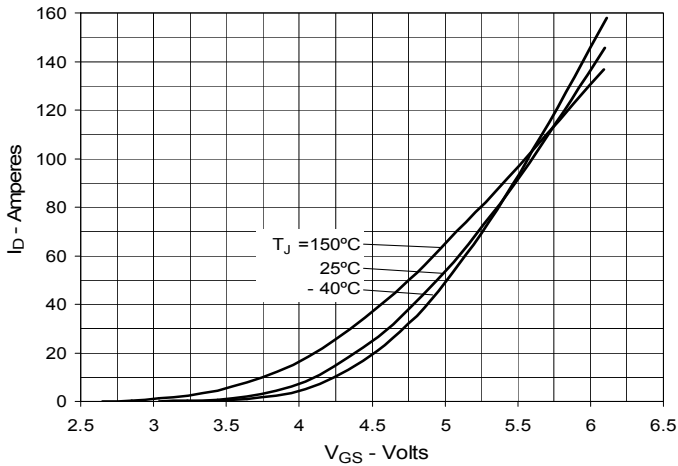


Fig. 8. Transconductance

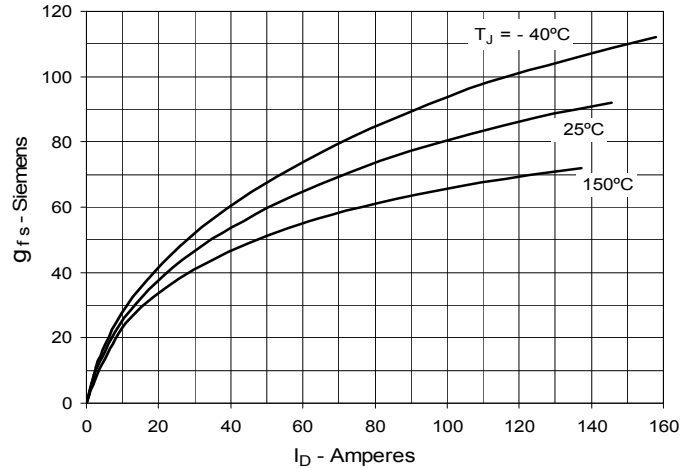


Fig. 9. Forward Voltage Drop of Intrinsic Diode

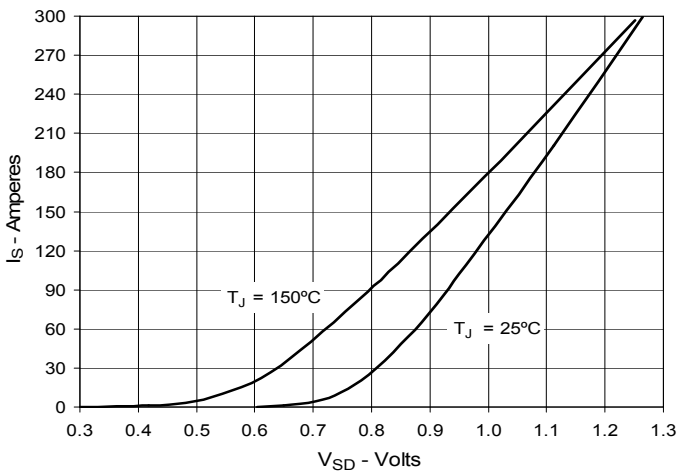


Fig. 10. Gate Charge

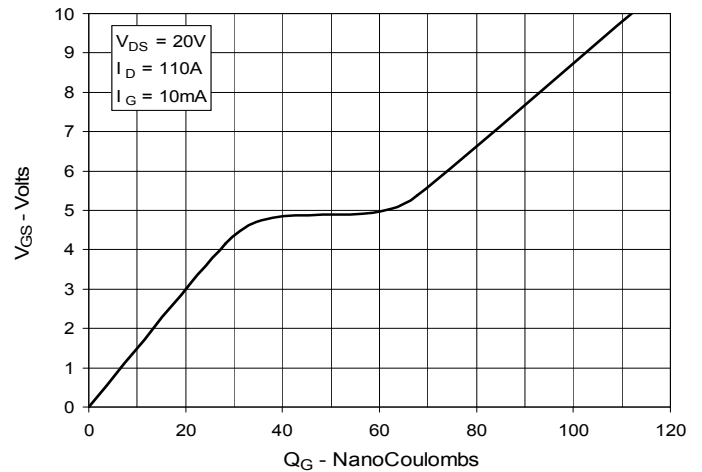


Fig. 11. Capacitance

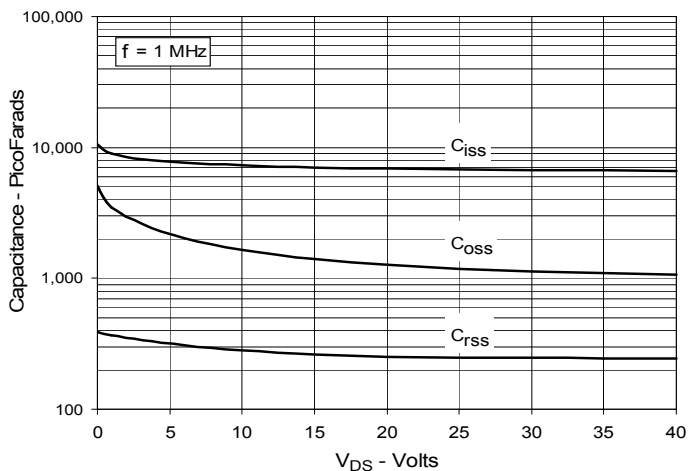


Fig. 12. Forward-Bias Safe Operating Area

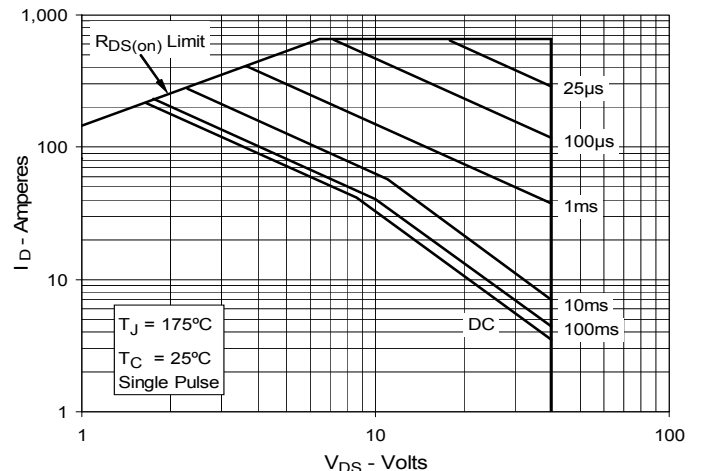


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

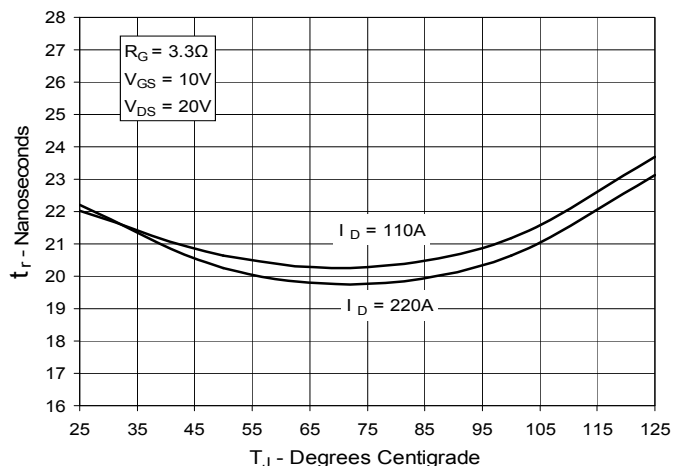


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

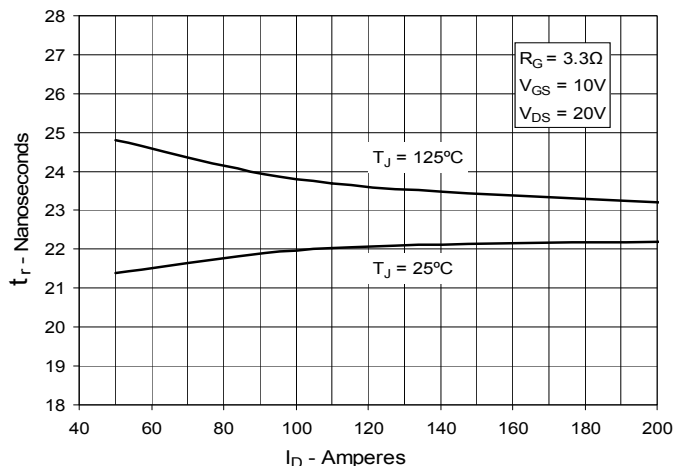


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

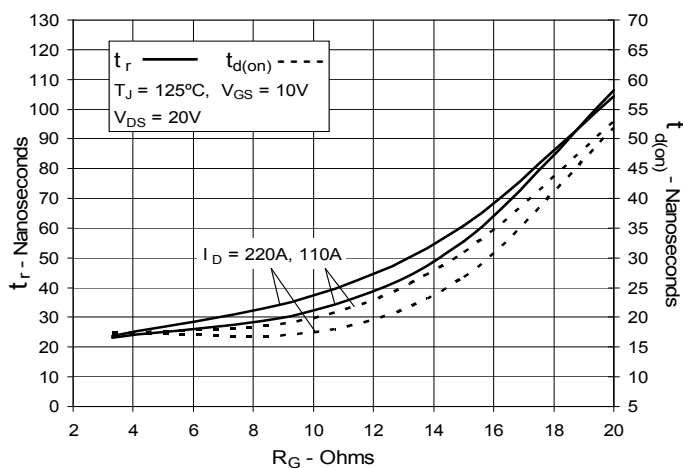


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

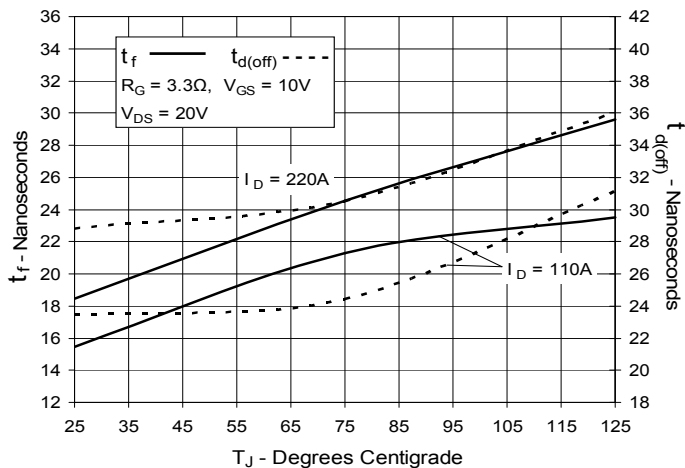


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

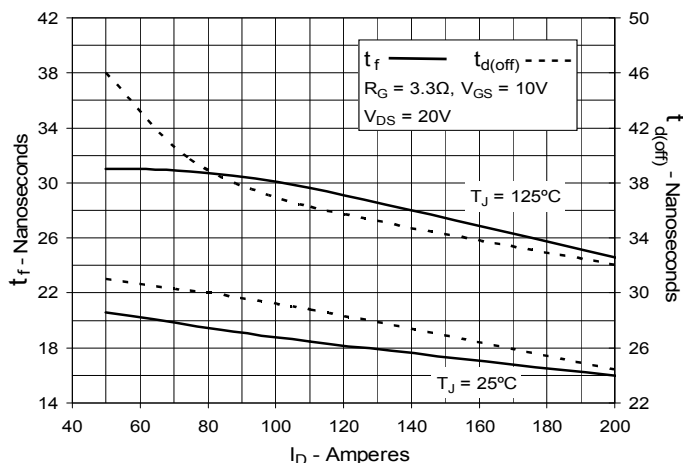


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

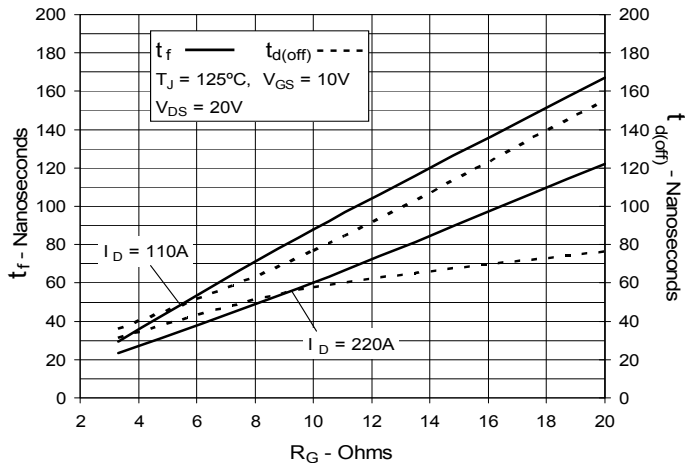


Fig. 19. Maximum Transient Thermal Impedance

